

Description

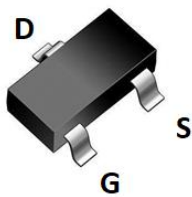
JMT P-channel Enhancement Mode Power MOSFET

Features

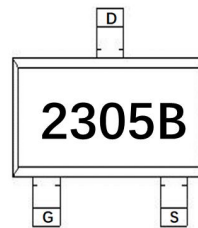
- $V_{DS} = -12V$, $I_D = -4.1A$
 $R_{DS(ON)} < 36m\Omega$ @ $V_{GS} = -4.5V$
 $R_{DS(ON)} < 53m\Omega$ @ $V_{GS} = -2.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

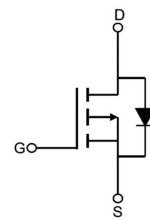
- PWM Applications
- Load Switch
- Power Management



SOT-23 top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
2305B	JMTL2305B	TAPING	SOT-23	7inch	3000	120000

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	-12	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	-4.1
		$T_C = 100^\circ C$	-2.6
I_{DM}	Pulsed Drain Current ^{note1}	-16	A
P_D	Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-12	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-12V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.65	-1.0	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} =-4.5V, I _D =-4.1A	-	26	36	mΩ
		V _{GS} =-2.5V, I _D =-3A	-	35	53	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -4V, V _{GS} = 0V, f = 1.0MHz	-	905	-	pF
C _{oss}	Output Capacitance		-	210	-	pF
C _{rss}	Reverse Transfer Capacitance		-	195	-	pF
Q _g	Total Gate Charge	V _{DS} = -4V, I _D = -4.1A, V _{GS} = -4.5V	-	7.8	15	nC
Q _{gs}	Gate-Source Charge		-	1.2	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	1.6	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -4V, I _D = -3.3A, R _G =1.0Ω, V _{GEN} =-4.5V, R _L =1.2Ω	-	13	20	ns
t _r	Turn-on Rise Time		-	35	53	ns
t _{d(off)}	Turn-off Delay Time		-	32	48	ns
t _f	Turn-off Fall Time		-	10	20	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-4.1	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-16	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -4.1A	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =-4.1A, di/dt=100A/μs	-	20	-	ns
Q _{rr}	Reverse Recovery Charge		-	9	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



Figure 1: Output Characteristics

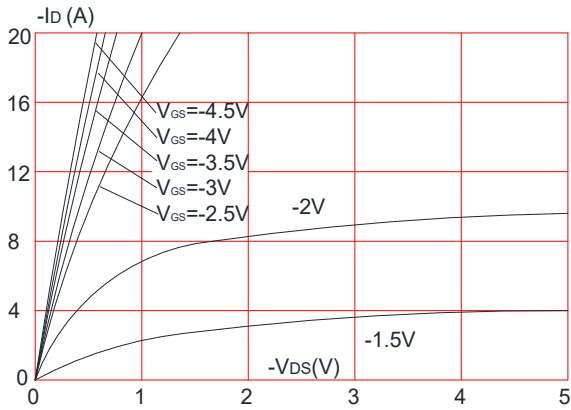


Figure 2: Typical Transfer Characteristics

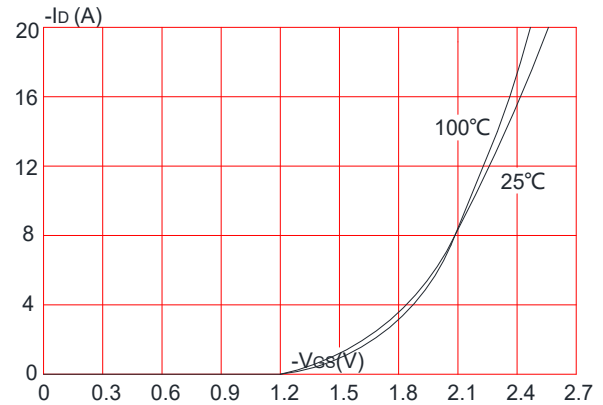


Figure 3: On-resistance vs. Drain Current

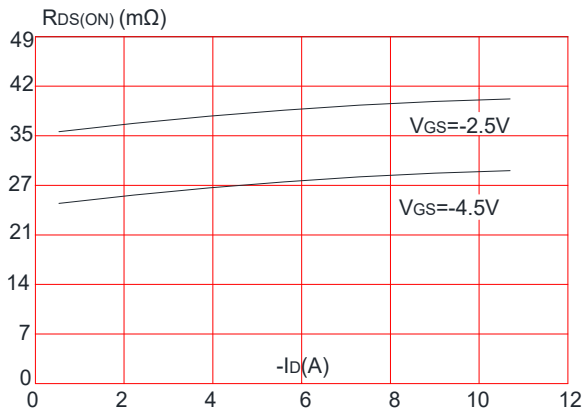


Figure 4: Body Diode Characteristics

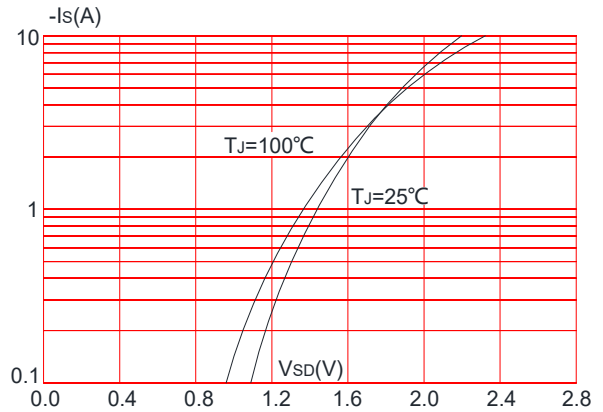


Figure 5: Gate Charge Characteristics

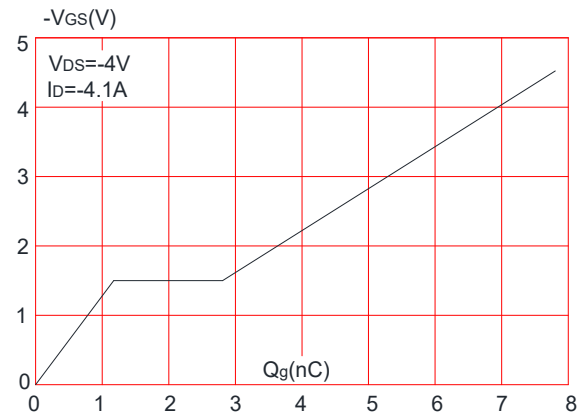


Figure 6: Capacitance Characteristics

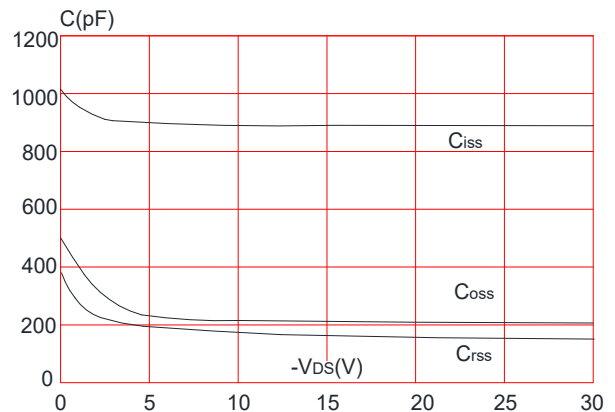




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

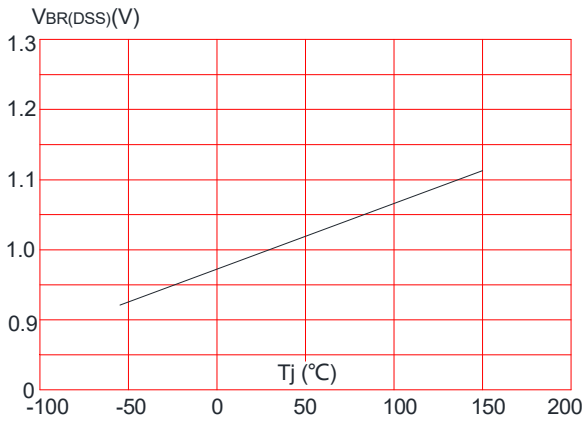


Figure 8: Normalized on Resistance vs. Junction Temperature

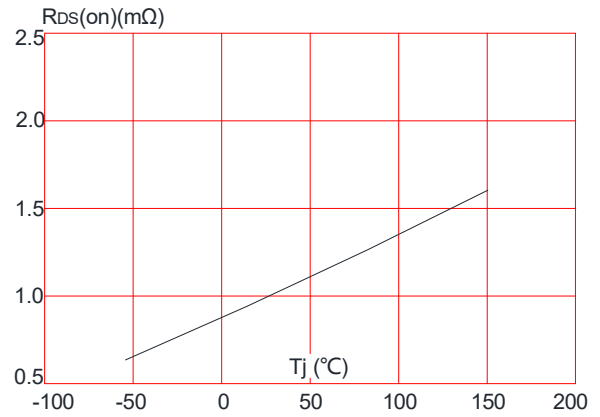


Figure 9: Maximum Safe Operating Area

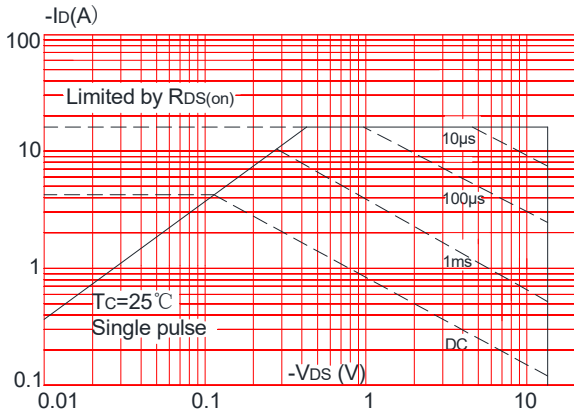


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

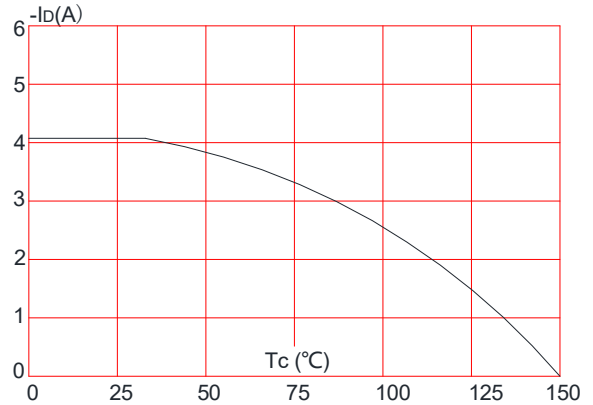
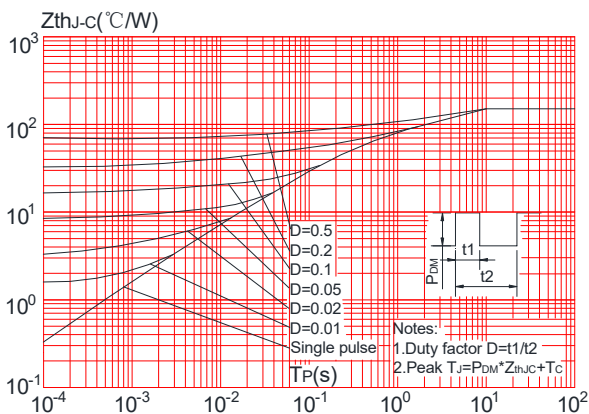
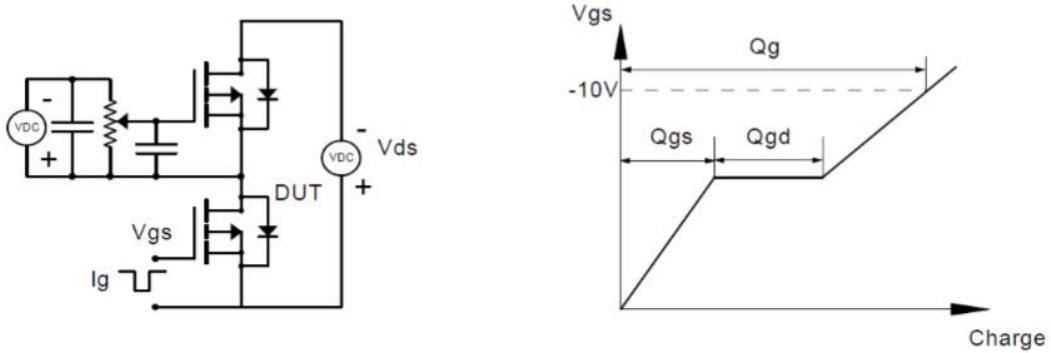


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

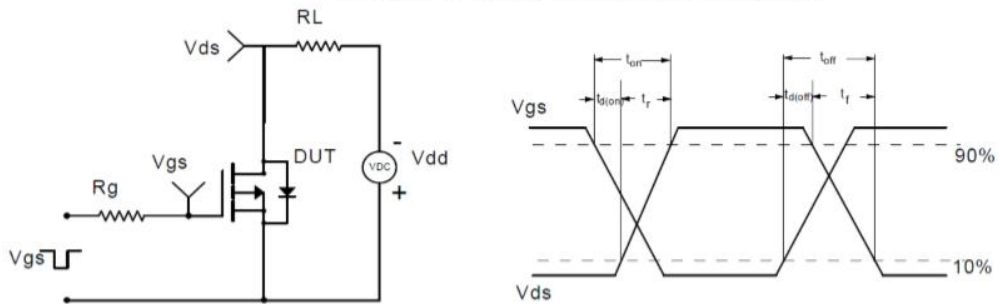


Test Circuit

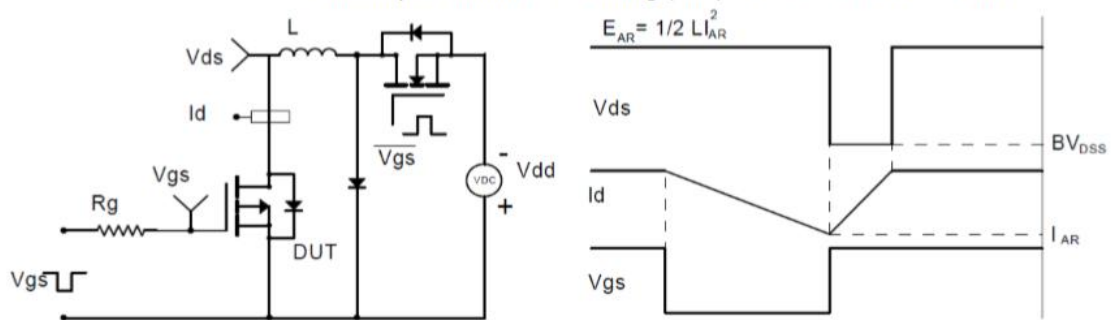
Gate Charge Test Circuit & Waveform



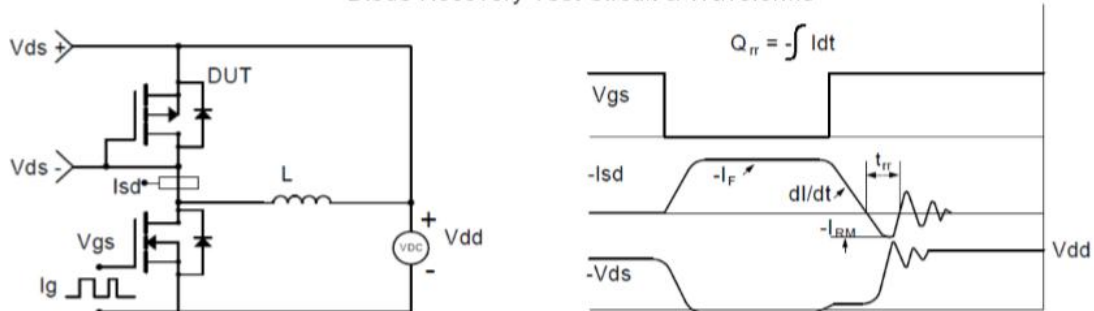
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

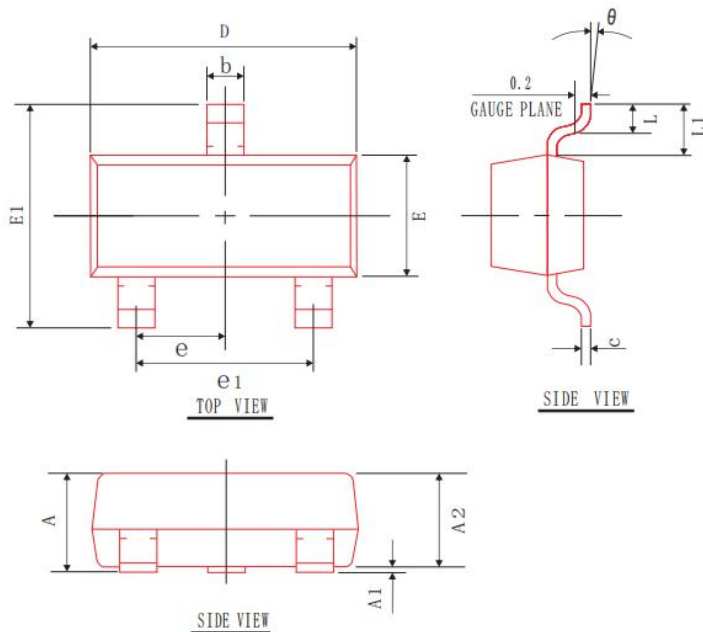


Diode Recovery Test Circuit & Waveforms





Package Mechanical Data-SOT-23



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.90	1.05	1.20
A1	0.00	0.05	0.10
A2	0.90	1.00	1.10
b	0.30	0.40	0.50
c	0.08	0.10	0.15
D	2.80	2.90	3.00
E	1.20	1.30	1.40
E1	2.30	2.40	2.50
L	0.30	0.40	0.50
θ	0°	5°	10°
L1	0.55 REF		
e	0.95 BSC		
e1	1.90 REF		

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